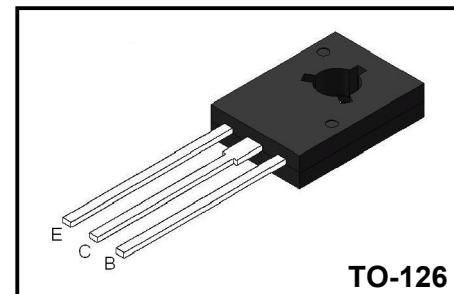


## NPN Plastic-Encapsulate Transistors

**Applications**

- ◆ Audio power amplifier
- ◆ DC-DC convertor
- ◆ Voltage regulator


**Features**

- ◆ High current output up to 4A
- ◆ Low saturation voltage
- ◆ Complement to BD441

**Absolute Maximum Rating ( $T_c=25^\circ\text{C}$  unless otherwise noted)**

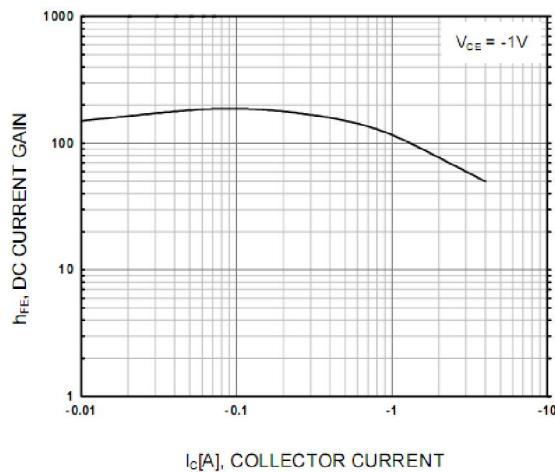
Parameter	Symbol	Value	Unit
Collector-base voltage	$\text{BV}_{\text{CBO}}$	80	V
Collector-emitter voltage	$\text{BV}_{\text{CEO}}$	80	V
Emitter-base voltage	$\text{BV}_{\text{EBO}}$	5	V
Collector current (DC)	$I_C$	4	A
Collector current (Pulse)	$I_{CP}$	7	A
Base current	$I_B$	1	A
Power dissipation	$T_A=25^\circ\text{C}$ $T_c=25^\circ\text{C}$	$P_C$	W
		25	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55~150	$^\circ\text{C}$

**Electrical Characteristics ( $T_c=25^\circ\text{C}$  unless otherwise noted)**

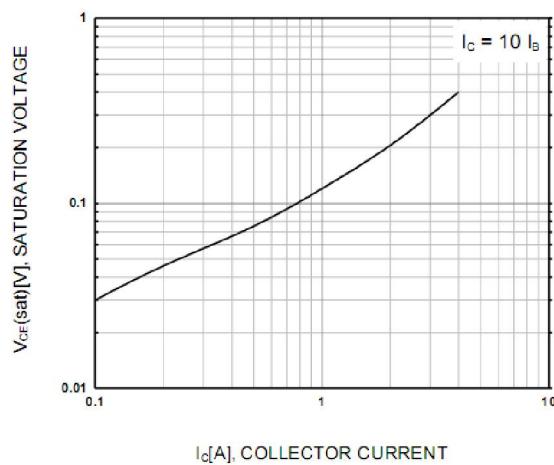
Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	$\text{BV}_{\text{CBO}}$	$I_C = 100\mu\text{A}, I_E = 0$	80			V
Collector-emitter breakdown voltage	$\text{BV}_{\text{CEO}}$	$I_C = 1\text{mA}, I_B = 0$	80			V
Emitter-base breakdown voltage	$\text{BV}_{\text{EBO}}$	$I_E = 100\mu\text{A}, I_C = 0$	5			V
Collector cut-off current	$I_{\text{CEO}}$	$V_{CB} = 80\text{V}, I_B = 0$			100	$\mu\text{A}$
Emitter cut-off current	$I_{\text{EBO}}$	$V_{EB} = 5\text{V}, I_C = 0$			100	$\mu\text{A}$
DC current gain*	$h_{FE1}$	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	20			
	$h_{FE2}$	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	40			
	$h_{FE3}$	$V_{CE} = 1\text{V}, I_C = 2\text{A}$	15			
Collector-emitter saturation voltage*	$V_{CE(\text{sat})}$	$I_C = 2\text{A}, I_B = 0.2\text{A}$		0.3	0.8	V
Base-emitter saturation voltage*	$V_{BE(\text{on})}$	$V_{CE} = 1\text{V}, I_C = 2\text{A}$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 1\text{V}, I_B = 250\text{mA}$	3			MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		45		pF

\* Pulse test: PW ≤ 300μs, duty cycle ≤ 2% Pulse

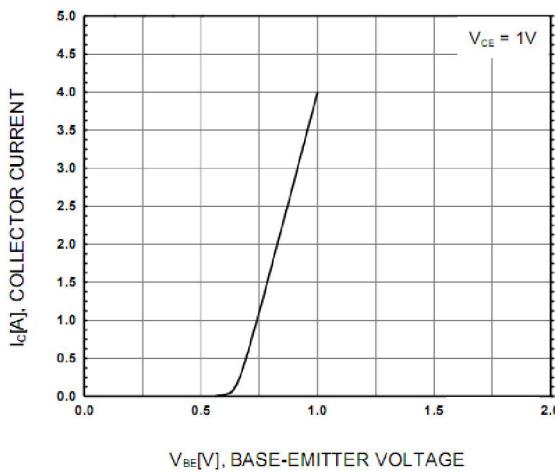
### Typical Characteristics



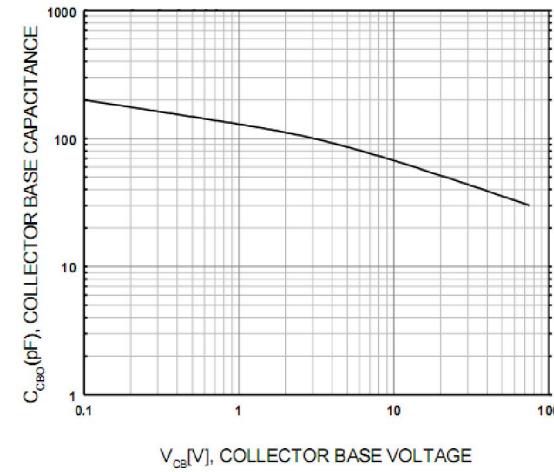
**Figure 1. DC current Gain**



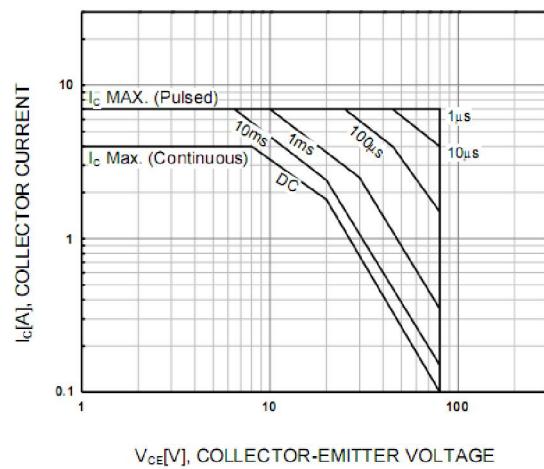
**Figure 2. Collector-Emitter Saturation Voltage**



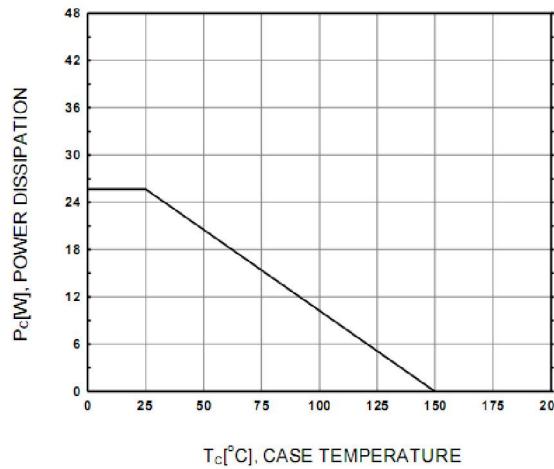
**Figure 3. Base-Emitter On Voltage**



**Figure 4. Collector-Base Capacitance**



**Figure 5. Safe Operating Area**



**Figure 6. Power Derating**

**Package Dimensions**

**TO-126**

Symbol	<b>Millimeter</b>		<b>Inches</b>	
	<b>Min.</b>	<b>Max.</b>	<b>Min.</b>	<b>Max.</b>
A	2.40	2.80	0.094	0.110
A1	1.00	1.40	0.039	0.055
b	0.66	0.86	0.026	0.034
b1	1.17	1.37	0.046	0.054
c	0.40	0.60	0.016	0.024
D	7.30	7.70	0.287	0.303
E	10.60	11.00	0.417	0.433
e	2.25	2.33	0.089	0.092
e1	4.50	4.66	0.177	0.183
L	14.00	15.00	0.551	0.591
L1	1.90	2.50	0.075	0.098
Φ	3.10	3.30	0.122	0.130

**ORDERING INFORMATION**

<b>Package</b>	<b>Packing Method</b>	<b>Pack</b>
TO-126	Bulk	500PCS/bag

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